ATP304

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P-Channel Power MOSFET -60V, -100A, 6.5mΩ, ATPAK

Features

- On-resistance $R_{DS}(on)1=5.0m\Omega(typ.)$
- Input Capacitance Ciss=13000pF(typ.)
- 4.5V drive
- Halogen Free compliance

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	V _{DSS}		-60	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-100	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-400	Α
Allowable Power Dissipation	PD	Tc=25°C	90	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		- 55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		656	mJ
Avalanche Current *2	I _{AV}		-75	Α

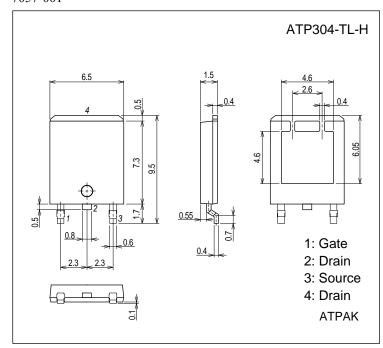
Note: *1 V_{DD} =-36V, L=100 μ H, I_{AV} =-75A

*2 L≤100µH, Single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

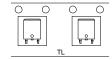
unit: mm (typ) 7057-001



Ordering & Package Information

Device	Package	Shipping	note
ATP304-TL-H	ATPAK	3,000 pcs. / reel	Pb-Free and Halogen-Free

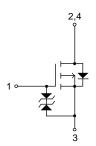
Packing Type: TL



Marking



Electrical Connection



Electrical Characteristics at $Ta = 25^{\circ}C$

Parameter	0	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0V	-60			٧
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-60V, V _{GS} =0V			-10	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	>
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-50A		100		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =-50A, V _G S=-10V		5.0	6.5	mΩ
	R _{DS} (on)2	I _D =-50A, V _G S=-4.5V		6.4	8.9	mΩ
Input Capacitance	Ciss			13000		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		1080		pF
Reverse Transfer Capacitance	Crss			760		pF
Turn-ON Delay Time	t _d (on)			80		ns
Rise Time	t _r	See Fig.2		650		ns
Turn-OFF Delay Time	t _d (off)			780		ns
Fall Time	tf			460		ns
Total Gate Charge	Qg			250		nC
Gate to Source Charge	Qgs	V _{DS} =-36V, V _{GS} =-10V, I _D =-100A		55		nC
Gate to Drain "Miller" Charge	Qgd			50		nC
Diode Forward Voltage	V _{SD}	I _S =-100A, V _G S=0V		-1.0	-1.5	٧
Reverse Recoverry Time	t _{rr}	See Fig.3		90		ns
Reverse Recoverry Charge	Q _{rr}	I _S =-100A, V _G _S = 0V, di/dt=100A/μs		245		nC

Fig.1 Unclamped Inductive Switching Test Circuit

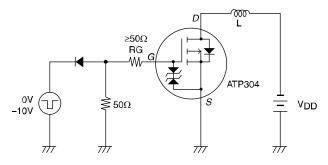


Fig.2 Switching Time Test Circuit

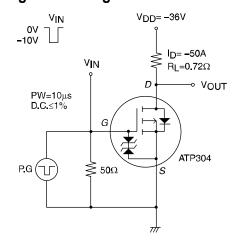
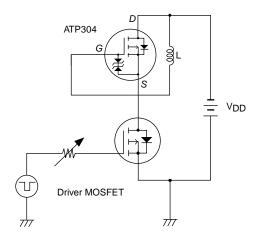
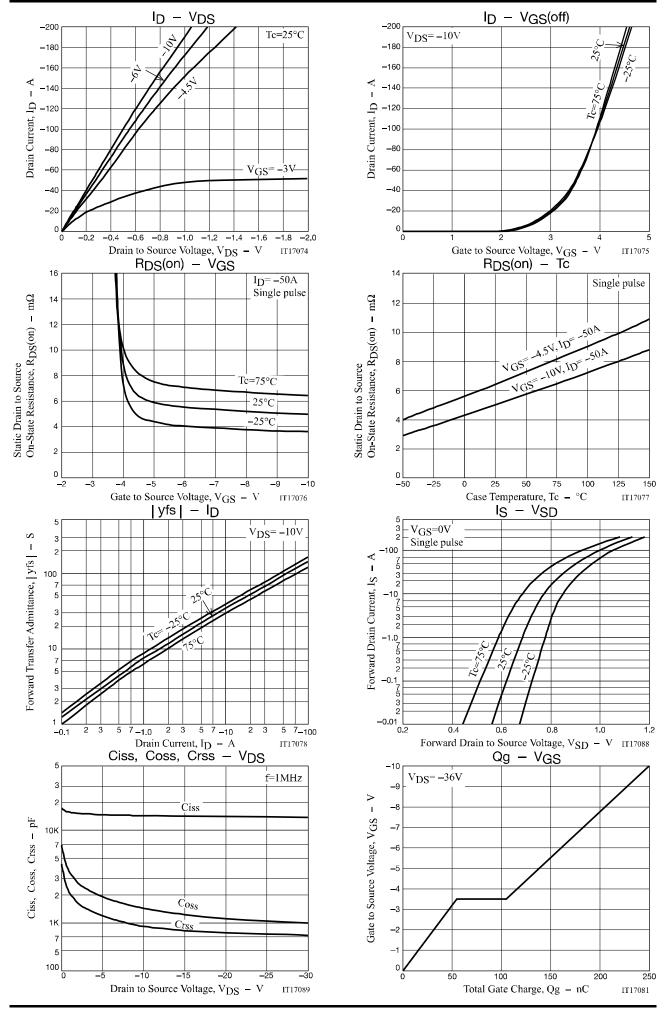
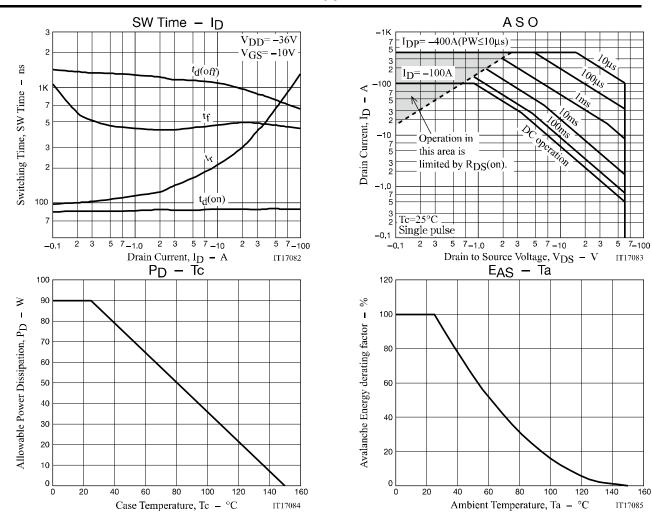


Fig.3 Reverse Recovery Time Test Circuit







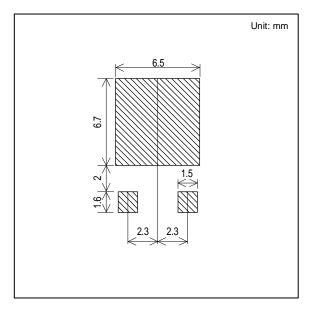
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Outline Drawing

ATP304-TL-H

Mass (g) Unit 0.266 For reference mm 6.540 IS 9.540 IS 0.440 IS

Land Pattern Example



Note on usage: Since the ATP304 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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